Dual N-Channel 30 V (D-S) MOSFET

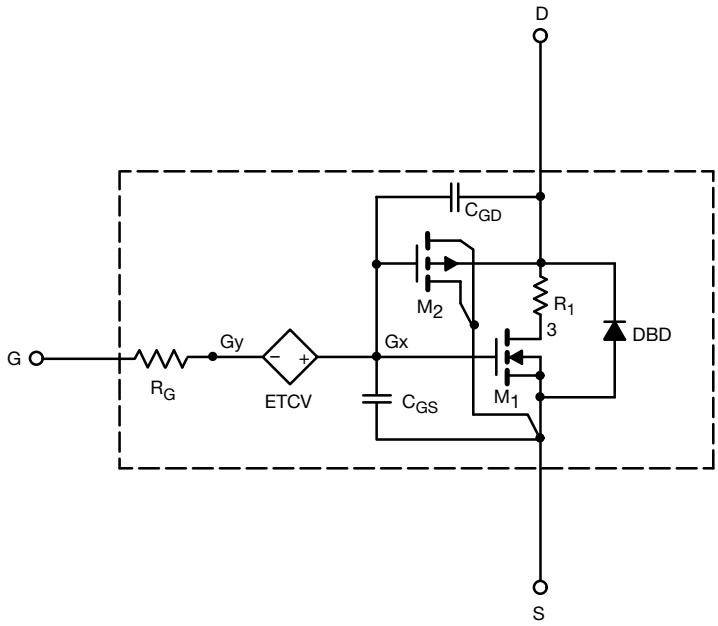
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

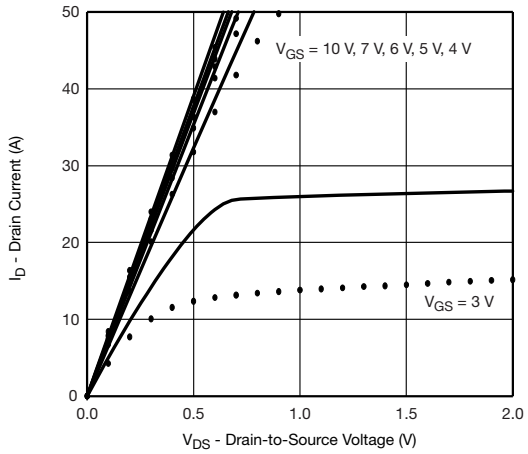
SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**SIMULATED DATA**	**MEASURED DATA**	**UNIT**
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	Ch-1	1.6	-	V
			Ch-2	1.7	-	
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 9.5 A	Ch-1	0.0128	0.0127	Ω
		V_{GS} = 10 V, I_D = 6.8 A	Ch-2	0.022	0.023	
		V_{GS} = 4.5 V, I_D = 8.7 A	Ch-1	0.0146	0.0146	
		V_{GS} = 4.5 V, I_D = 6.1 A	Ch-2	0.028	0.028	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 9.5 A	Ch-1	57	43	S
		V_{DS} = 15 V, I_D = 6.8 A	Ch-2	22	17	
Diode Forward Voltage[a]	V_{SD}	I_S = 7.6 A	Ch-1	0.77	0.82	V
		I_S = 5.5 A	Ch-2	0.82	0.85	
Dynamic[b]						
Input Capacitance	C_{iss}	Channel 1 V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz Channel 2 V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	Ch-1	1000	1000	pF
			Ch-2	369	366	
Output Capacitance	C_{oss}		Ch-1	231	215	
			Ch-2	82	82	
Reverse Transfer Capacitance	C_{rss}		Ch-1	86	85	
			Ch-2	45	45	
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 9.5 A	Ch-1	16	17.2	nC
		V_{DS} = 15 V, V_{GS} = 10 V, I_D = 6.8 A	Ch-2	6.5	7.3	
Gate-Source Charge	Q_{gs}	Channel 1 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 9.5 A Channel 2 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 6.8 A	Ch-1	8.4	8.4	
			Ch-2	3.5	3.6	
			Ch-1	3	3	
			Ch-2	1.1	1.1	
Gate-Drain Charge	Q_{gd}		Ch-1	2.6	2.6	
			Ch-2	1.3	1.3	

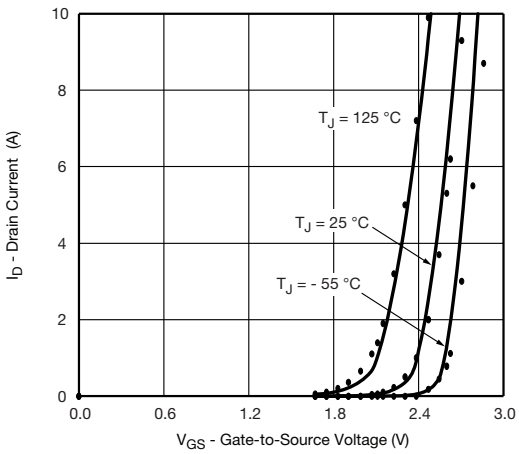
Notes

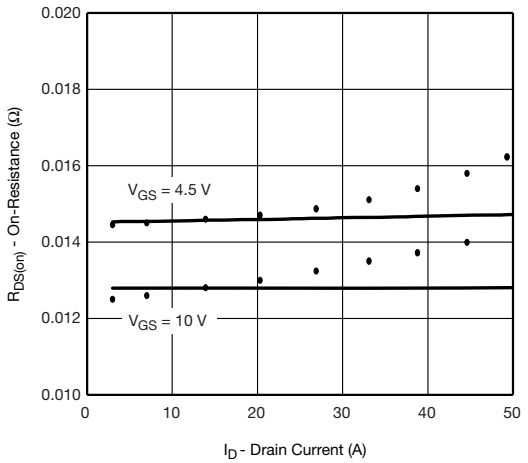
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

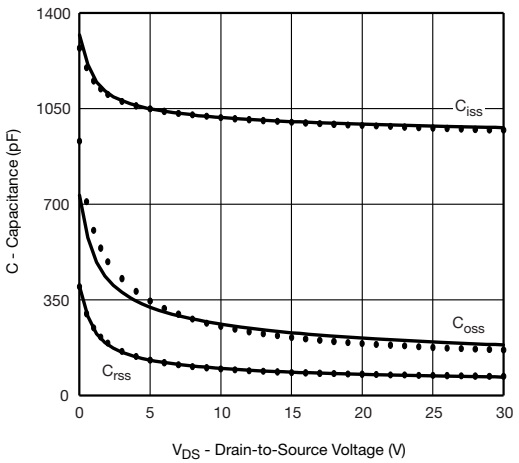
b. Guaranteed by design, not subject to production testing.

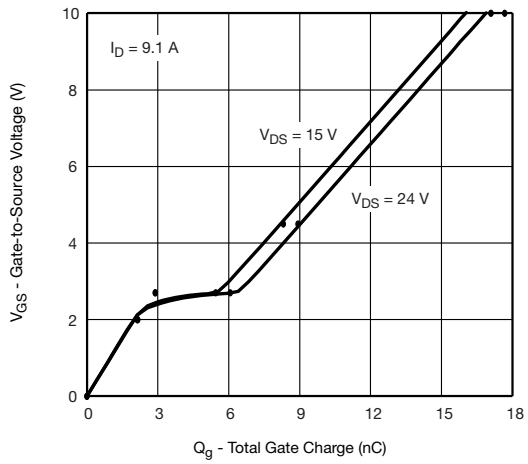
COMPARISON OF MODEL WITH MEASURED DATA T_J = 25 °C, unless otherwise noted
Channel 1

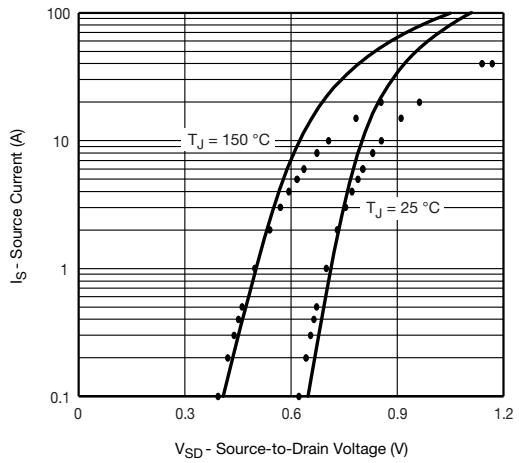








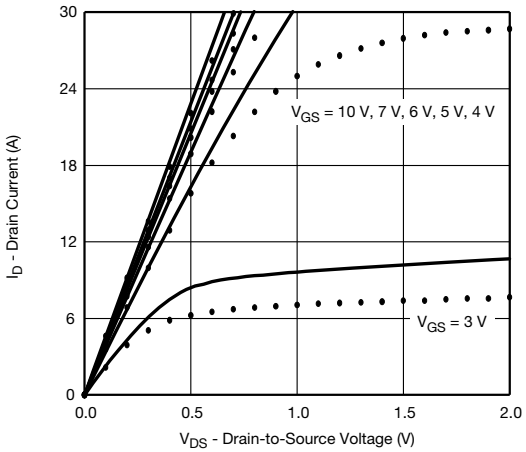


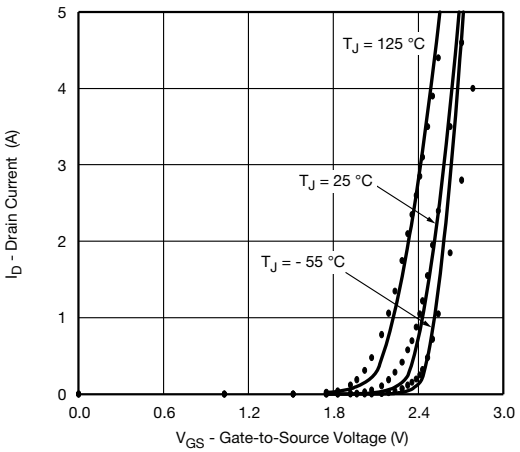


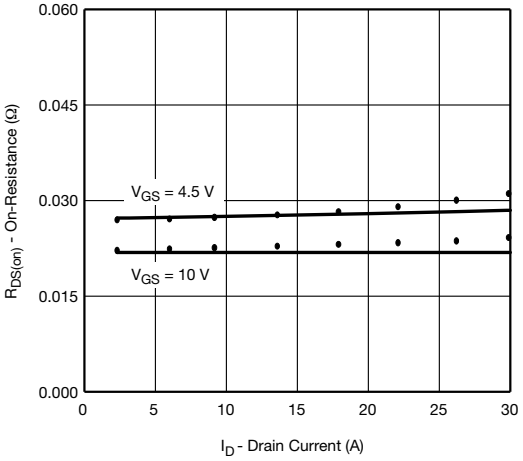
Note
Dots and squares represent measured data.

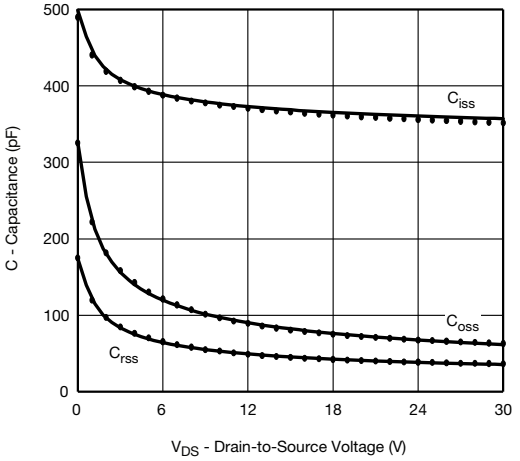
COMPARISON OF MODEL WITH MEASURED DATA T_J = 25 °C, unless otherwise noted

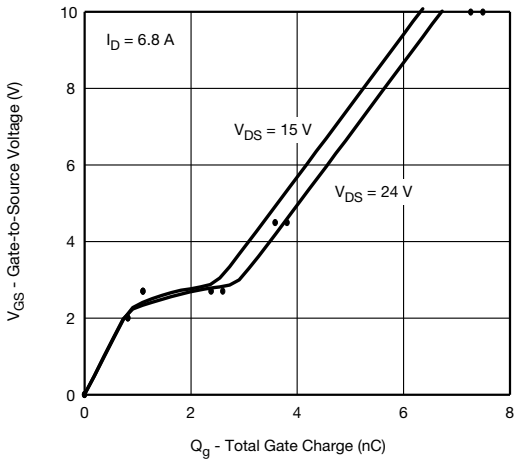
Channel 2

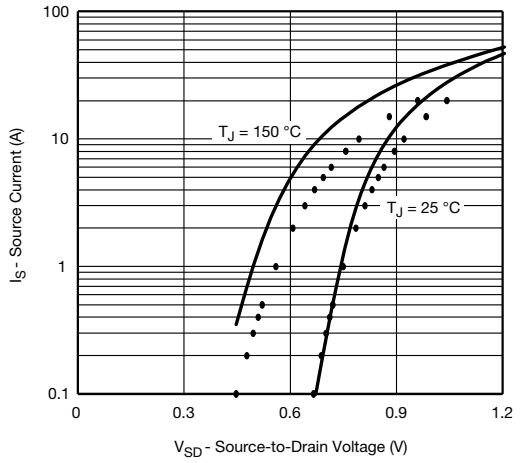












Note

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